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(71) Applicant (for all designated States except US): **NATIONAL UNIVERSITY OF SINGAPORE** [SG/SG];
21 Lower Kent Ridge Road, Singapore 119077 (SG).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **CHEN, Wei** [CN/SG]; c/o National University of Singapore, Faculty of Science, Department of Chemistry, 21 Lower Kent Ridge Road, Singapore 119077 (SG). **CHEN, Zhenyu** [CN/SG]; c/o National University of Singapore, Faculty of Science, Department of Chemistry, 21 Lower Kent Ridge Road, Singapore 119077 (SG). **WEE, Thye Shen Andrew** [SG/SG]; c/o National University of Singapore, Faculty of Science, Department of Physics, 21 Lower Kent Ridge Road, Singapore 119077 (SG). **XIE, Lanfei** [CN/SG]; c/o National University of Singapore, Faculty of Science, Department of Physics, 21 Lower Kent Ridge Road, Singapore 119077 (SG). **WANG, Xiao** [CN/SG]; c/o National University of Singapore, Faculty of Science, Department of Physics, 21 Lower Kent Ridge Road, Singapore 119077 (SG). **SUN, Jiatao** [CN/SG]; c/o National University of Singapore, Faculty of Science, Department

of Chemistry, 21 Lower Kent Ridge Road, Singapore 119077 (SG). **ARIANDO** [ID/SG]; c/o National University of Singapore, Faculty of Science, Department of Physics, 21 Lower Kent Ridge Road, Singapore 119077 (SG).

(74) Agent: **AMICA LAW LLC**; 30 Raffles Place, #18-03/04 Chevron House, Singapore 048622 (SG).

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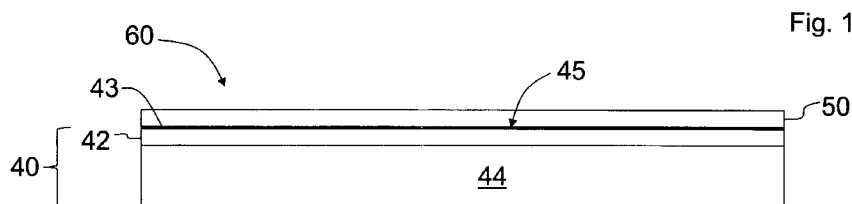
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(54) Title: HOLE DOPING OF GRAPHENE



(57) Abstract: An article includes a layer of graphene having a first work function; and a metal oxide film disposed on the layer of graphene, the metal oxide film having a second work function greater than the first work function. Electrons are transferred from the layer of graphene to the metal oxide film, forming a hole accumulation layer in the layer of graphene.

